

Customer No.: 31561
Application No.: 10/710,818
Docket NO.:14217-US-PA-X

AMENDMENT

Please amend the application as indicated hereafter.

In the Claims :

Claim 1 (previously presented) An electrostatic discharge (ESD) protection device, comprising:

an ESD protection circuit, comprising:

at least a diode connected in series between a first voltage and a pad; and

at least an ESD component connected in series between a second voltage and a pad, wherein each of the at least an ESD component comprises a deep N-well region formed in a P-type substrate, a triple P-well formed in the deep N-well region, and a highly doped N-type (N+) region and a highly doped P-type (P+) region formed in the triple P-well region.

Claim 2 (original) The ESD protection device of claim 1, wherein when a number of the ESD component is one, the N+ region of the ESD component is connected to the pad, and the P+ region of the ESD component is connected to the second voltage.

Claim 3 (original) The ESD protection device of claim 1, wherein when a number of the ESD component is two including a 1st ESD component and a 2nd ESD component, the N+ region of a 1st ESD component is connected to the pad, the P+ region of the 2nd ESD component is connected to the second voltage, and the P+ region of the 1st

Customer No.: 31561
Application No.: 10/710,818
Docket NO.:14217-US-PA-X

ESD component is connected to the N+ region of the 2nd ESD component.

Claim 4 (original) The ESD protection device of claim 1, wherein when a number of the ESD component is S including a 1st ESD component to a Sth ESD component, the N+ region of the 1st ESD component is connected to the pad, the P+ region of the Sth ESD component is connected to the second voltage, and the P+ region of the Tth ESD component is connected to the N+ region of the (T+1)th ESD component, wherein S is a positive integer and T is a positive integer from 1 to S-1.

Claim 5 (original) The ESD protection device of claim 1, wherein each of the at least a diode comprises a N-well region formed in a P-type substrate, and a N+ region and a P+ region formed in the N-well region.

Claim 6 (original) The ESD protection device of claim 1, wherein when a number of the diode is one, the N+ region of the diode is connected to the first voltage, and the P+ region of the diode is connected to the pad.

Claim 7 (original) The ESD protection device of claim 1, wherein when a number of the diode is two including a first diode and a second diode, the N+ region of a first diode is connected to the first voltage, the P+ region of the second diode is connected to the pad, and the P+ region of the first diode is connected to the N+ region of the second diode.

Customer No.: 31561
Application No.: 10/710,818
Docket NO.:14217-US-PA-X

Claim 8 (original) The ESD protection device of claim 1, wherein when a number of the diode is S including a 1st diode to a Sth diode, the N+ region of the 1st diode is connected to the first voltage, the P+ region of the Sth diode is connected to the pad, and the P+ region of the Tth diode is connected to the N+ region of the (T+1)th diode, wherein S is a positive integer and T is a positive integer from 1 to S-1.

Claim 9 (previously presented) The of claim 1, wherein the ESD protection device further comprises another ESD protection circuit comprising:

a PMOS transistor; and

an NMOS transistor, wherein a gate of the PMOS transistor and a gate of the NMOS transistor are connected to the pad, a source of the PMOS transistor is connected to a drain of the NMOS transistor, a drain of the PMOS transistor is connected to the first voltage, and a source of the NMOS transistor is connected to the second voltage.

Claim 10 (original) The ESD protection device of claim 1, wherein the ESD protection device is a radio frequency (RF) ESD protection device.

Claims 11-19 (canceled)